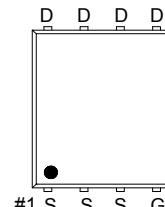
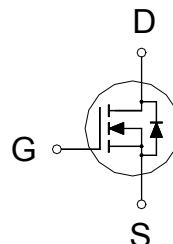


NIKO-SEM
**N-Channel Enhancement Mode
Field Effect Transistor**
**PK6A6BA
PDFN 5x6P
Halogen-Free & Lead-Free**
PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
40V	8mΩ	42A



G. GATE
D. DRAIN
S. SOURCE

**ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	42	A
	$T_C = 100^\circ\text{C}$		26.6	
Pulsed Drain Current ¹		I_{DM}	100	
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	11	A
	$T_A = 70^\circ\text{C}$		9	
Avalanche Current		I_{AS}	33.7	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	56.8	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	31	W
	$T_C = 100^\circ\text{C}$		12.5	
Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2.3	W
	$T_A = 70^\circ\text{C}$		1.5	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		54	°C / W
Junction-to-Case	$R_{\theta JC}$		4	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	40			V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.3	1.8	2.3	
Gate-Body Leakage	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 32\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
		$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}, T_J = 55^\circ\text{C}$			10	
Drain-Source On-State Resistance ¹	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 11\text{A}$		6.4	12	$\text{m}\Omega$
		$V_{\text{GS}} = 10\text{V}, I_D = 11\text{A}$		5.5	8	
Forward Transconductance ¹	g_{fs}	$V_{\text{DS}} = 5\text{V}, I_D = 11\text{A}$		55		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 15\text{V}, f = 1\text{MHz}$		1672		pF
Output Capacitance	C_{oss}			206		
Reverse Transfer Capacitance	C_{rss}			124		
Gate Resistance	R_g	$V_{\text{GS}} = 0\text{V}, V_{\text{DS}} = 0\text{V}, f = 1\text{MHz}$		1.3		Ω
Total Gate Charge ²	Q_g	$V_{\text{GS}} = 10\text{V}$		34		nC
		$V_{\text{GS}} = 4.5\text{V}$		18		
Gate-Source Charge ²	Q_{gs}	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 11\text{A}$		5.1		nS
Gate-Drain Charge ²	Q_{gd}			8.3		
Turn-On Delay Time ²	$t_{\text{d}(\text{on})}$			25		
Rise Time ²	t_r			11		
Turn-Off Delay Time ²	$t_{\text{d}(\text{off})}$	$V_{\text{DS}} = 15\text{V}, I_D \approx 11\text{A}, V_{\text{GS}} = 10\text{V}, R_{\text{GEN}} = 6\Omega$		41		nS
Fall Time ²	t_f			12		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ\text{C}$)						
Continuous Current	I_S				24	A
Forward Voltage ¹	V_{SD}	$I_F = 11\text{A}, V_{\text{GS}} = 0\text{V}$			1.3	V
Reverse Recovery Time	t_{rr}	$I_F = 11\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		19.5		nS
Reverse Recovery Charge	Q_{rr}			9.4		nC

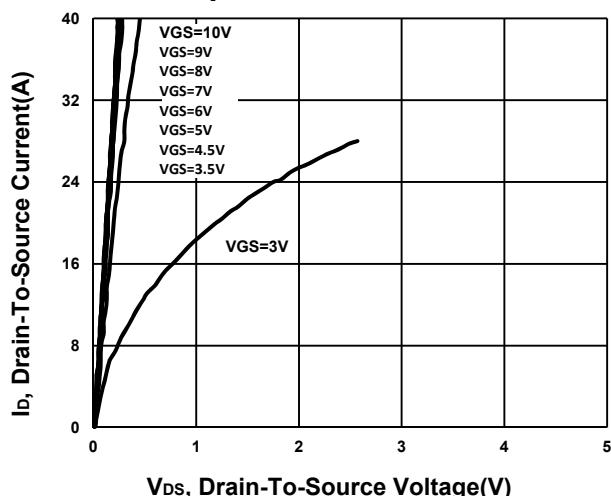
¹Pulse test : Pulse Width $\leq 300\ \mu\text{sec}$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.

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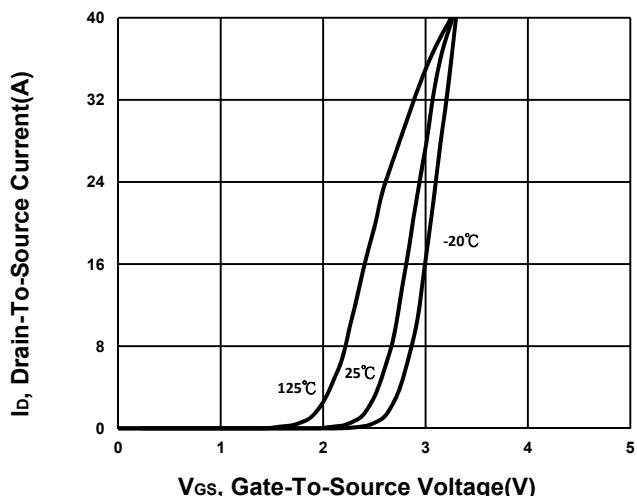
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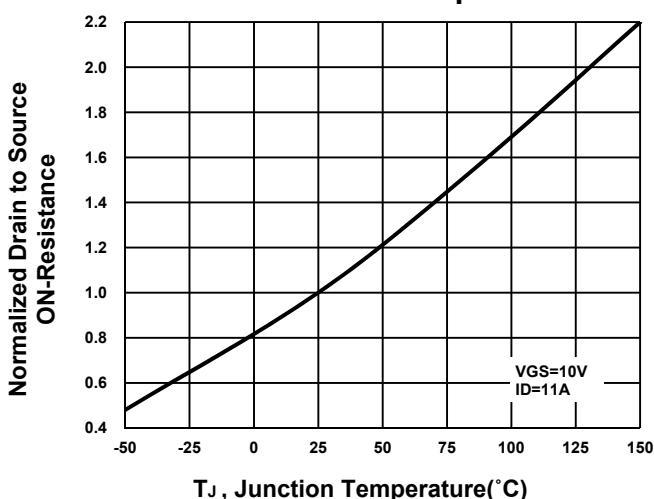
Output Characteristics



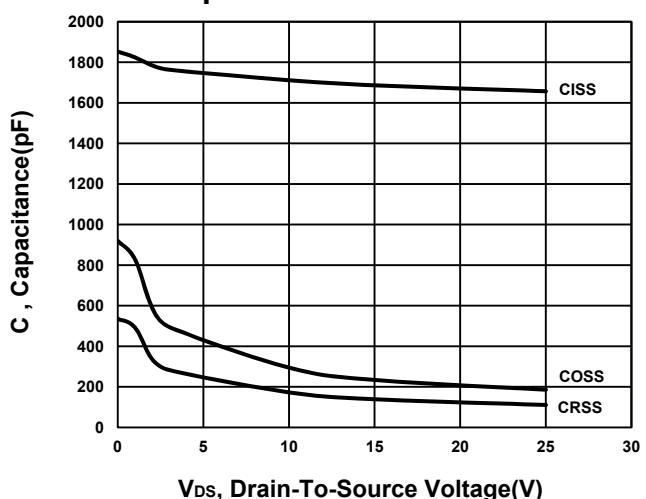
Transfer Characteristics



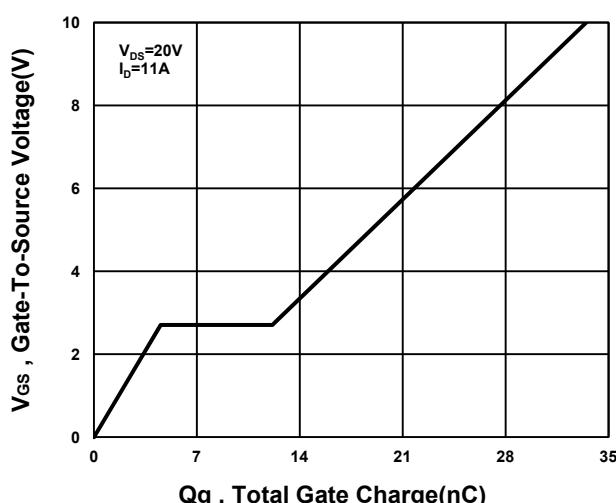
On-Resistance VS Temperature



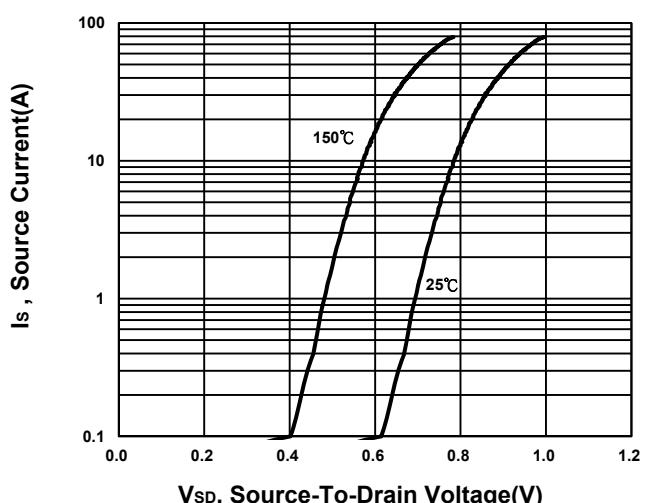
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



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